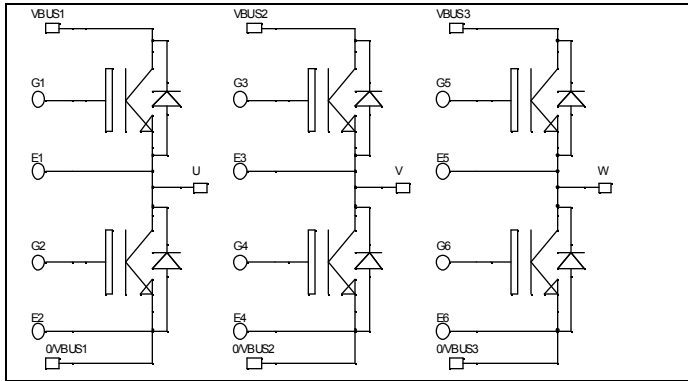


**Triple phase leg
Trench + Field Stop IGBT[®]
Power Module**

**$V_{CES} = 1700V$
 $I_C = 50A @ T_c = 80^\circ C$**

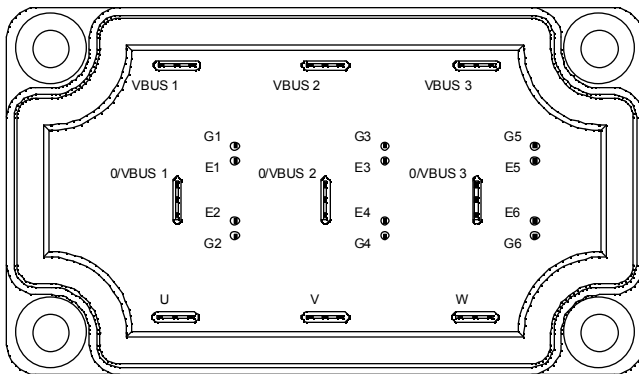


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT[®] Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Kelvin emitter for easy drive



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1700	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	70
		$T_c = 80^\circ C$	50
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	310
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	100A @ 1600V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1700\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 50\text{A}$		2.0	2.4	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		4400		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		180		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		150		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		370		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 50\text{A}$		40		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50\text{A}$		650		
T_f	Fall Time	$R_G = 10\Omega$		180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		400		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 50\text{A}$		50		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50\text{A}$		800		
T_f	Fall Time	$R_G = 10\Omega$		250		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15\text{V}$ $V_{Bus} = 900\text{V}$ $I_C = 50\text{A}$	$T_j = 125^\circ\text{C}$	16		mJ
E_{off}	Turn-off Switching Energy	$R_G = 10\Omega$	$T_j = 125^\circ\text{C}$	15		

Diode ratings and characteristics

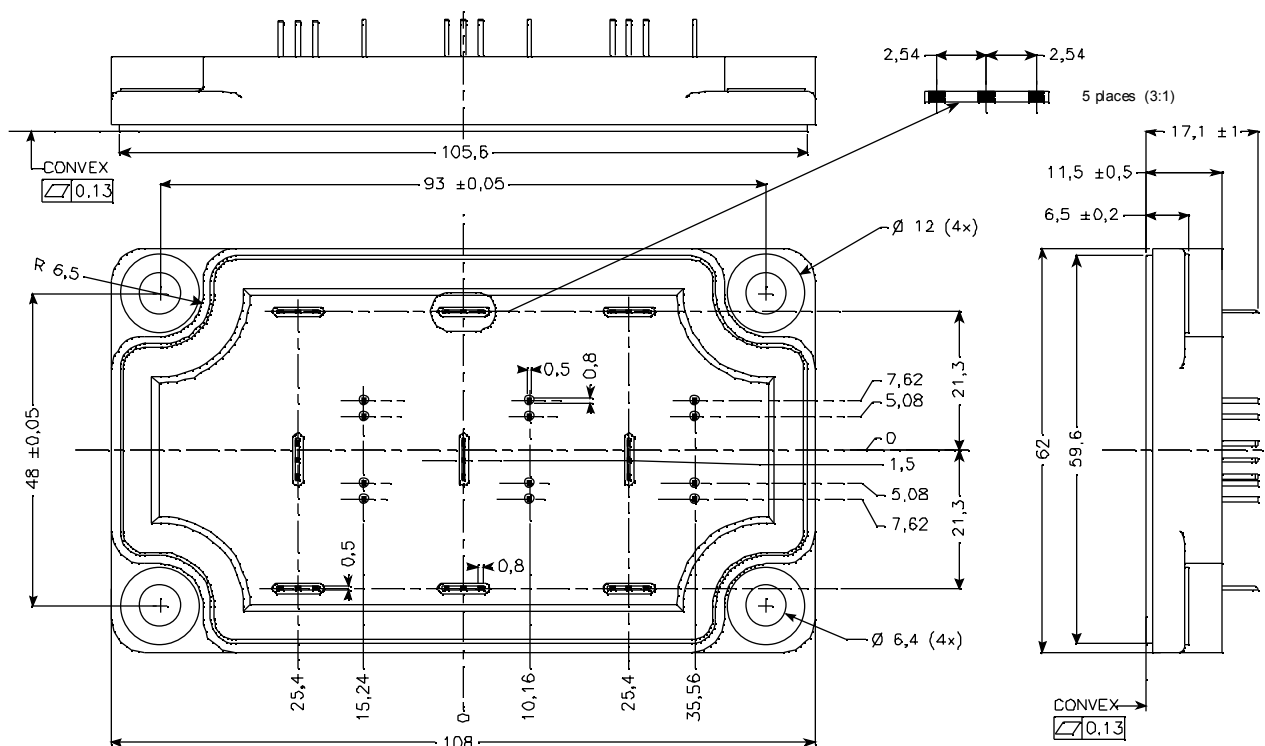
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1700\text{V}$			250	μA
					500	
I_F	DC Forward Current			50		A
V_F	Diode Forward Voltage	$I_F = 50\text{A}$		1.8	2.2	V
				1.9		
t_{rr}	Reverse Recovery Time	$I_F = 50\text{A}$ $V_R = 900\text{V}$ $di/dt = 800\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	385		ns
			$T_j = 125^\circ\text{C}$	490		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	14		μC
			$T_j = 125^\circ\text{C}$	23		
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	6		mJ
			$T_j = 125^\circ\text{C}$	12		

Thermal and package characteristics

Symbol Characteristic

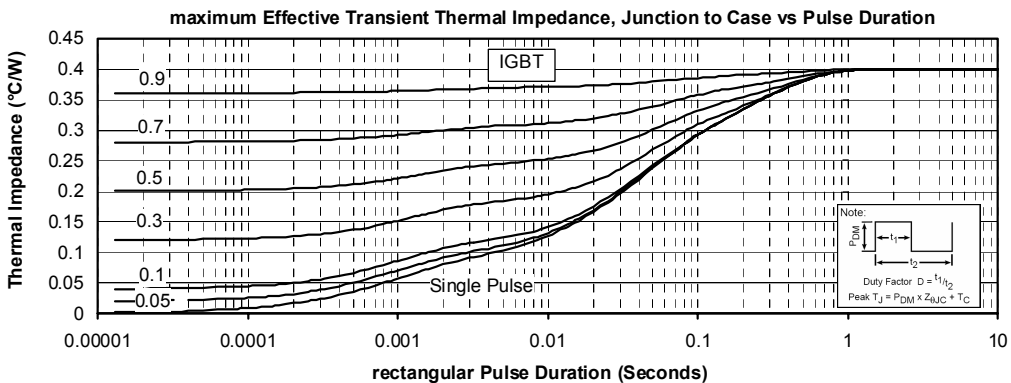
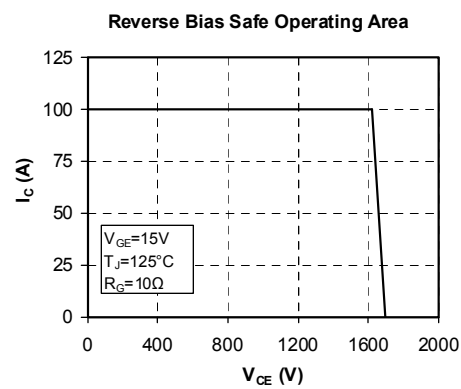
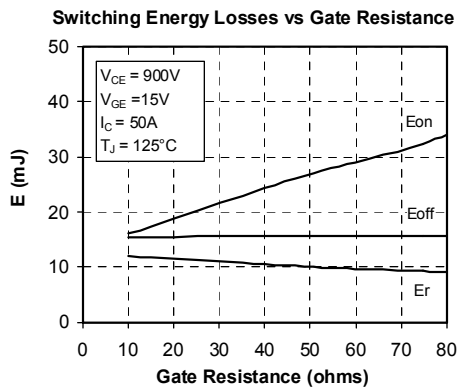
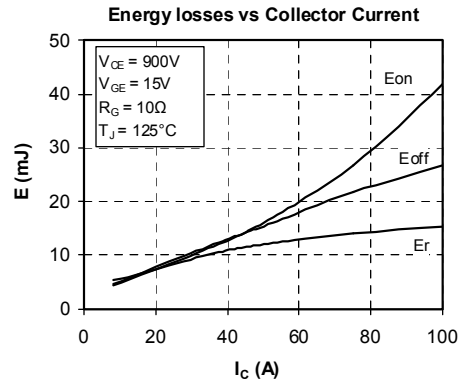
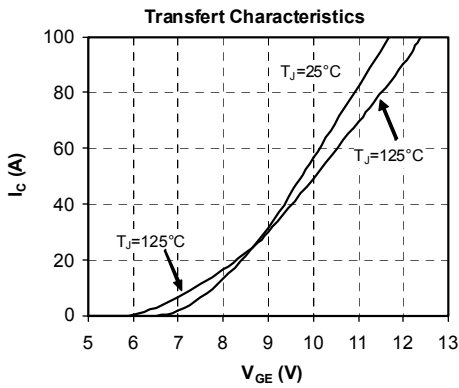
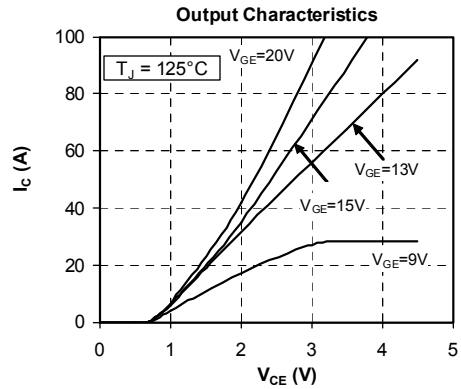
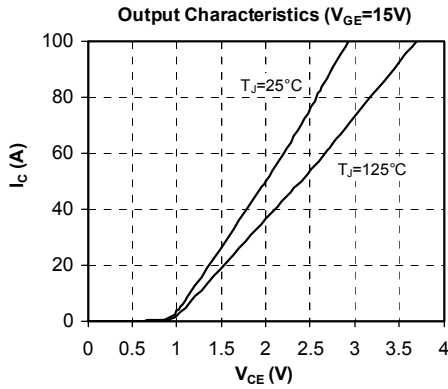
		Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.4	°C/W	
		Diode		0.7		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	3500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package Weight				250	g

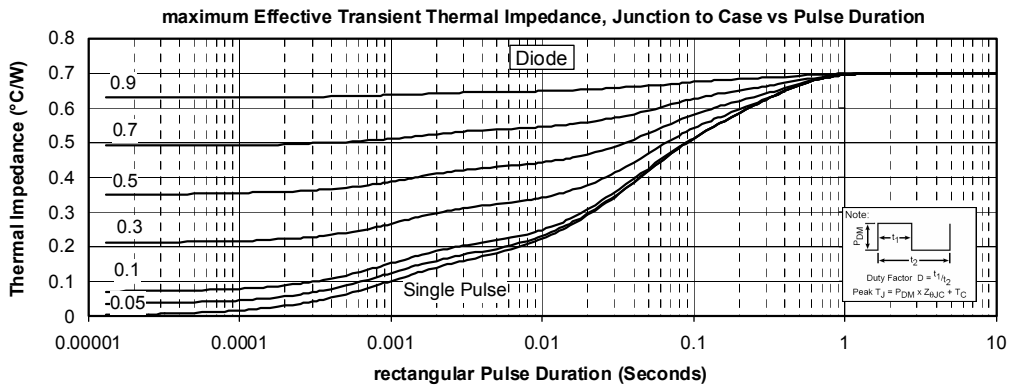
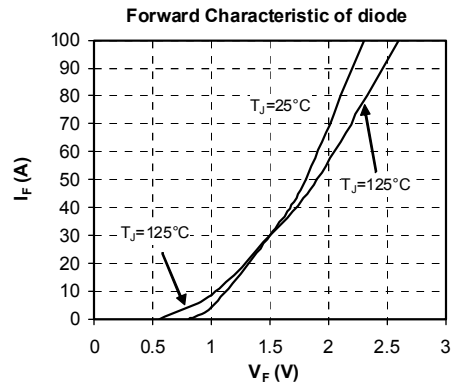
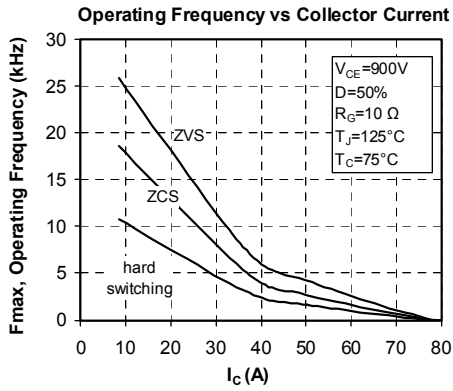
SP6-P Package outline (dimensions in mm)



See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.